

# **MD1812**

# **High-Speed Quad-MOSFET Driver**

#### Features

- · 6 ns Rise and Fall Time
- 2A Peak Output Source and Sink Currents
- 1.8V to 5V Input CMOS Compatible
- Smart Logic Threshold
- Low-jitter Design
- · Four Matched Channels
- Drives Two P-channel and Two N-channel MOSFETs
- Outputs can Swing below Ground
- · Built-in Level Translator for Negative Gate Bias
- User-defined damping for Return-to-zero Application
- · Low-inductance Quad-flat No-lead Package
- · High-performance Thermally Enhanced Package

#### Applications

Package Type

- Ultrasound PN Code Transmitter
- Medical Ultrasound Imaging
- Piezoelectric Transducer Drivers
- Non-destructive Testing
- High-speed Level Translator
- High-voltage Bipolar Pulser

#### **General Description**

The MD1812 is a high-speed quad-MOSFET driver designed to drive two P-channel and two N-channel high-voltage MOSFETs for medical ultrasound applications and other applications requiring a high-output current for a capacitive load. The input stage of the MD1812 is a high-speed level translator that is able to operate from logic input signals of 1.8V to 5V amplitude. An adaptive threshold circuit is used to set the level translator switch threshold to the average of the input logic 0 and logic 1 levels. The level translator uses a proprietary circuit which provides DC coupling together with high-speed operation.

The output stage of the MD1812 has separate power connections, enabling the output signal L and H levels to be chosen independently from the supply voltages used for the majority of the circuit. As an example, the input logic levels may be 0V and 1.8V, the control logic may be powered by +5V and -5V, and the output L and H levels may be varied anywhere over the range of -5V to +5V. The output stage is capable of peak currents of up to ±2A, depending on the supply voltages used and load capacitance present. The OE pin serves a dual purpose. First, its logic H level is used to compute the threshold voltage level for the channel input level translators. Second, when OE is low, the outputs are disabled, with the A and C outputs high and the B and D outputs low. This assists in properly pre-charging the AC coupling capacitors that may be used in series in the gate drive circuit of an external PMOS and NMOS transistor pair. A built-in level shifter provides PMOS gate negative bias drive. This enables the user-defined damping control to generate return-to-zero bipolar output pulses.

	<b>16-lead QFN</b> (Top view)	
See Table 2-1 for pin information.		

## **Functional Block Diagram**



## **Typical Application Circuit**



# 1.0 ELECTRICAL CHARACTERISTICS

#### Absolute Maximum Ratings†

Supply Voltage, V <sub>DD</sub> –V <sub>SS</sub>	–0.5V to +13.5V
Output High Supply Voltage, V <sub>H</sub>	
Output Low Supply Voltage, VL	$V_{SS}^{-}$ -0.5V to $V_{H}^{-}$ +0.5V
Low-side Supply Voltage, V <sub>SS</sub>	–7V to +0.5V
Supply Voltage, V <sub>DD</sub> -V <sub>NEG</sub>	–0.5V to +20V
Negative Supply Voltage, V <sub>NEG</sub> -V <sub>SS</sub>	
Logic Input Levels	V <sub>SS</sub> -0.5V to GND +7V
Operating Junction Temperature, T <sub>1</sub>	–25°C to +125°C
Storage Temperature, T <sub>S</sub>	–65°C to +150°C
Power Dissipation	
ESD Rating (Note 1)	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: Device is ESD sensitive. Handling precautions are recommended.

# DC ELECTRICAL CHARACTERISTICS

<b>Electrical Specifications:</b> $V_H = V_{DD} = 12V$ , $V_L = V_{SS} = GND = 0V$ , $V_{NEG} = -6V$ , $V_{OE} = 3.3V$ and $T_J = 25^{\circ}C$										
Parameter		Sym.	Min.	Тур.	Max.	Unit	Conditions			
Supply Voltage		V <sub>DD</sub> –V <sub>SS</sub>	4.5	_	13	V	2.5V ≤ V <sub>DD</sub> ≤ 13V			
Supply Voltage		V <sub>DD</sub> –V <sub>NEG</sub>	_	_	18	V				
Low-side Supply Voltage		V <sub>SS</sub>	-5.5	_	0	V				
Output High Supply Voltag	ge	V <sub>H</sub>	V <sub>SS</sub> +2	—	V <sub>DD</sub>	V				
Output Low Supply Voltag	le	VL	V <sub>SS</sub>	_	V <sub>DD</sub> - 2	V				
Negative Supply Voltage		V <sub>NEG</sub>	-9	_	V <sub>SS</sub> –2	V	May be connected to V <sub>SS</sub> if OUTG is not used			
V <sub>DD</sub> Quiescent Current		I <sub>DDQ</sub>	_	1.5	_	mA				
V <sub>H</sub> Quiescent Current		I <sub>HQ</sub>		_	10	μA	No input transitions, OE = 1			
V <sub>NEG</sub> Quiescent Current		I <sub>NEGQ</sub>	_	150		μA				
V <sub>DD</sub> Average Current		I <sub>DD</sub>	_	7		mA	One channel on at 5			
V <sub>H</sub> Average Current		Ι <sub>Η</sub>	_	22	_	mA	MHz,			
V <sub>NEG</sub> Average Current		I <sub>NEG</sub>	_	1.5	_	mA	no load			
Input Logic Voltage High		V <sub>IH</sub>	V <sub>OE</sub> 0.3	_	5	V				
Input Logic Voltage Low		V <sub>IL</sub>	0	—	0.3	V	For logic inputs INA, INB,			
Input Logic Current High		I <sub>IH</sub>	_	—	1	μA	INC and IND			
Input Logic Current Low		Ι <sub>ΙL</sub>	_	—	1	μA				
OE Input Logic Voltage Hi	gh	V <sub>IH</sub>	1.7	—	5	V				
OE Input Logic Voltage Lo	W	V <sub>IL</sub>	0	_	0.3	V	For logic input OE			
OE Input Resistance	R <sub>IN</sub>	10	20	30	kΩ					
Logic Input Capacitance		C <sub>IN</sub>	_	5	10	pF				
Output Sink Desistance	OUTA-D	D	_	_	12.5	Ω	I <sub>SINK</sub> = 50 mA			
Output Sink Resistance	OUTG	R <sub>SINK</sub>	_	_	200	12	I <sub>SINK</sub> = 5 mA			
Output Source	OUTA-D	Р	_	—	12.5	0	I <sub>SOURCE</sub> = 50 mA			
Resistance	OUTG	R <sub>SOURCE</sub>			200	Ω	I <sub>SOURCE</sub> = 5 mA			

# DC ELECTRICAL CHARACTERISTICS (CONTINUED)

<b>Electrical Specifications:</b> $V_H = V_{DD} = 12V$ , $V_L = V_{SS} = GND = 0V$ , $V_{NEG} = -6V$ , $V_{OE} = 3.3V$ and $T_J = 25^{\circ}C$									
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions			
Peak Output Sink Current	I <sub>SINK</sub>	_	2		Α				
Peak Output Source Current	I <sub>SOURCE</sub>	_	2		А				

# AC ELECTRICAL CHARACTERISTICS

<b>Electrical Specifications:</b> $V_H = V_{DD} = 12V$ , $V_L = V_{SS} = GND = 0V$ , $V_{NEG} = -6V$ , $V_{OE} = 3.3V$ and $T_A = 25^{\circ}C$									
Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions			
Input or OE Rise and Fall Time	t <sub>irf</sub>	—		10	ns	Logic input edge speed requirement			
Propagation Delay INC to OUTG	t <sub>PCG</sub>	_	40	_	ns	10 M $\Omega$ load to GND			
Propagation Delay when Output is from Low to High for OUTA-D	t <sub>PLH</sub>	_	7	_	ns				
Propagation Delay when Output is from High to Low for OUTA-D	t <sub>PHL</sub>	_	7	_	ns	C <sub>LOAD</sub> = 1000 pF, input signal rise/fall time of 2 ns			
Output Rise Time	t <sub>r</sub>	—	6		ns				
Output Fall Time	t <sub>f</sub>	_	6	_	ns				
Rise and Fall Time Matching	l t <sub>r</sub> —t <sub>f</sub> l	—	1	_	ns				
Propagation Low-to-high and High-to-low Matching	I t <sub>PLH</sub> -t <sub>PHL</sub> I	_	1	_	ns	For each channel			
Propagation Delay Matching	∆t <sub>dm</sub>	—	±2	_	ns	Device-to-device delay match			
Output Enable Time	t <sub>OE_ON</sub>		200		ns				
	t <sub>OE_OFF</sub>	—	9	—	ns				

# **TEMPERATURE SPECIFICATIONS**

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions		
TEMPERATURE RANGE								
Operating Junction Temperature	ТJ	-25	_	125	°C			
Storage Temperature	Τ <sub>S</sub>	-65	_	150	°C			
PACKAGE THERMAL RESISTANCE								
16-lead QFN	$\theta_{JA}$	—	25		°C/W	Note 1		

**Note 1:** 1 oz. 4-layer 3" x 4" PCB

# MD1812

#### **Timing Diagram**



#### TABLE 1-1: TRUTH FUNCTION TABLE

	Logic Inputs		Outputs				
OE	INA	INB	OL	OUTB			
Н	L	L	V	′н	V <sub>H</sub>		
Н	L	Н	V	VL			
Н	Н	L	١	V <sub>H</sub>			
Н	Н	Н	١	VL			
L	Х	Х	V	′н	VL		
OE	INC	IND	OUTC	OUTG	OUTD		
Н	L	L	V <sub>H</sub>	V <sub>SS</sub>	V <sub>H</sub>		
Н	L	Н	V <sub>H</sub>	V <sub>SS</sub>	VL		
Н	Н	L	VL	V <sub>NEG</sub>	V <sub>H</sub>		
Н	Н	Н	VL	V <sub>NEG</sub>	VL		
L	Х	Х	V <sub>H</sub>	V <sub>SS</sub>	VL		

#### 2.0 PIN DESCRIPTION

The details on the pins of MD1812 are listed on Table 2-1. See **Package Type** for the location of pins.

Pin Number	Pin Name	Description
1	INB	Logic input. Controls OUTB when OE is high.
2	VL	Supply voltage for N-channel output stage
3	GND	Device ground
4	VNEG	Supply voltage for the auxiliary gate drive (Note 1)
5	INC	Logic input. Controls OUTC when OE is high.
6	IND	Logic input. Controls OUTD when OE is high.
7	VSS	Supply voltage for low-side analog, level shifter and gate drive circuit
8	OUTD	Output driver
9	OUTC	Output driver
10	OUTG	Auxiliary output driver
11	VH	Supply voltage for P-channel output stage
12	OUTB	Output driver
13	OUTA	Output driver
14	VDD	Supply voltage for high-side analog, level shifter and gate drive circuit
15	INA	Logic input. Controls OUTA when OE is high.
16	OE	Output enable logic input

TABLE 2-1: PIN FUNCTION TABLE

**Note 1:** Thermal pad and pin 4, VNEG must be connected externally.

### 3.0 APPLICATION INFORMATION

For proper operation of the MD1812, low-inductance bypass capacitors should be used on the various supply pins. The GND input pin should be connected to the logic ground. The INA, INB, INC, IND and OE pins should be connected to a logic source with a swing of GND to V<sub>CC</sub>, where V<sub>CC</sub> is 1.8V to 5V. When the input logic(s) is high, the output(s) will swing to V<sub>1</sub>, and when the input(s) logic is low, the output(s) will swing to  $V_{H}$ . All inputs must be kept low until the device is powered up. Good trace practices should be followed corresponding to the desired operating speed. The internal circuitry of the MD1812 is capable of operating up to 100 MHz, with the primary speed limitation being the loading effect of the load capacitance. Because of this speed and the high transient currents due to the capacitive loads, the bypass capacitors should be as close to the chip pins as possible. Unless the load specifically requires bipolar drive, the  $V_{SS}$  and  $V_{L}$  pins should have a low-inductance bypass capacitor to GND and supply power connections. If these voltages are not zero, they need bypass capacitors in a manner similar to the positive power supplies. The power connection  $V_{DD}$  should have a ceramic bypass capacitor to the ground plane with short leads and decoupling components to prevent resonance in the power leads.

Output drivers OUTA and OUTC drive the gate of an external P-channel MOSFET, while output drivers OUTB and OUTD drive the gate of an external N-channel MOSFET, and they all swing from V<sub>H</sub> to V<sub>L</sub>. The auxiliary output drive, OUTG, swings from V<sub>SS</sub> to V<sub>NEG</sub> and drives the gate of an external P-channel MOSFET through a 2 k $\Omega$  series resistor.

The voltages of  $V_H$  and  $V_L$  decide the output logic levels. These two pins can draw fast transient currents of up to 2A, so they should be provided with a suitable bypass capacitor located next to the chip pins. A ceramic capacitor of up to 1 µF may be appropriate, with a series ferrite bead to prevent resonance in the power supply lead going to the capacitor. Pay particular attention to minimizing trace lengths, current loop area and using sufficient trace width to reduce inductance. Surface-mount components are highly recommended. Since the output impedance of this driver is very low, in some cases, it may be desirable to add a small series resistor in series with the output signal to obtain better waveform transitions at the load terminals. This will reduce the output voltage slew rate at the terminals of a capacitive load.

The OE pin sets the threshold level of logic for inputs  $(V_{OE} + V_{GND})/2$ . When OE is low, OUTA and OUTC are at  $V_{H}$ , while OUTB and OUTD are at  $V_{L}$ . Auxiliary output OUTG is at  $V_{SS}$ , regardless of the inputs INA and INB.

Ensure that parasitic couplings are minimized from the driver output to the input signal terminals. The parasitic feedback may cause oscillations or spurious waveform shapes on the edges of signal transitions. Since the input operates with signals down to 1.8V, even small coupled voltages may cause problems. The use of a solid ground plane and good power and signal layout practices will prevent this problem. Make sure that the circulating ground return current from a capacitive load will not react with common inductance and cause noise voltages in the input logic circuitry. Best timing performance is obtained for OUTC when the voltage of  $V_{SS}-V_{NEG} = V_H-V_L$ .

## 4.0 PACKAGING INFORMATION

## 4.1 Package Marking Information



Legenc	I: XXX Y YY WW NNN @3 *	Product Code or Customer-specific information Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC <sup>®</sup> designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.
Note:	be carried	nt the full Microchip part number cannot be marked on one line, it will over to the next line, thus limiting the number of available characters at code or customer-specific information. Package may or not include rate logo.

# 16-Lead QFN Package Outline (K6)

4.00x4.00mm body, 1.00mm height (max), 0.65mm pitch



Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Notes: 1. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

Depending on the method of manufacturing, a maximum of 0.15mm pullback (L1) may be present.

2. 3. The inner tip of the lead may be either rounded or square.

Symb	ol	А	A1	A3	b	D	D2	E	E2	е	L	L1	θ
	MIN	0.80	0.00		0.25	3.85*	2.50	3.85*	2.50		0.30†	0.00	<b>0</b> 0
Dimension (mm)	NOM	0.90	0.02	0.20 REF	0.30	4.00	2.65	4.00	2.65	0.65 BSC	0.40†	-	-
()	MAX	1.00	0.05		0.35	4.15*	2.80	4.15*	2.80	200	0.50 <sup>†</sup>	0.15	14 <sup>0</sup>

JEDEC Registration MO-220, Variation VGGC-2, Issue K, June 2006.

\* This dimension is not specified in the JEDEC drawing. † This dimension differs from the JEDEC drawing.

Drawings not to scale.

#### APPENDIX A: REVISION HISTORY

#### Revision A (May 2017)

- Converted Supertex Doc# DSFP-MD1812 to Microchip DS20005746A
- · Changed the package marking format
- Changed the quantity of the 16-lead QFN K6 package from 3000/Reel to 3300/Reel
- Made minor text changes throughout the document

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PART NO.	<u>. xx</u>		- <u>x</u> - <u>x</u>	Example:	
Device	Packa Option		Environmental Media <sup>'</sup> Type	a) MD1812K6-G:	High-Speed Quad-MOSFET Driver, 16-lead QFN, 3300/Reel
Device:	MD1812	=	High-Speed Quad-MOSFET Driver		
Package:	K6	=	16-lead QFN		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	3300/Reel for a K6 Package		

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